

# MA2SD10

## Silicon epitaxial planar type

For super-high speed switching circuit

### ■ Features

- Sealed in the super small SS-mini type 2-pin package
- Allowing to rectify under ( $I_{F(AV)} = 200$  mA) condition
- Low forward rise voltage  $V_F$
- Allowing high-density mounting

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	20	V
Repetitive peak reverse voltage	$V_{RRM}$	20	V
Non-repetitive peak forward surge current*	$I_{FSM}$	1	A
Peak forward current	$I_{FM}$	300	mA
Average forward current	$I_{F(AV)}$	200	mA
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

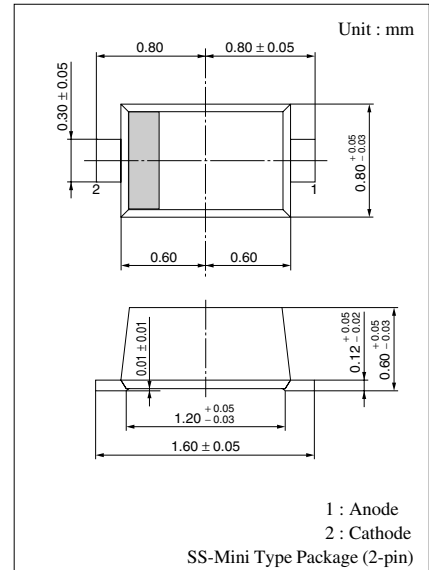
Note) \* : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 10$ V			20	$\mu\text{A}$
Forward voltage (DC)	$V_{F1}$	$I_F = 5$ mA			0.27	V
	$V_{F2}$	$I_F = 200$ mA			0.47	V
Terminal capacitance	$C_t$	$V_R = 0$ V, $f = 1$ MHz		40		pF

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 250 MHz



Marking Symbol: 2L

Internal Connection

